Abstracts

High-isolation series-shunt FET SPDT switch with a capacitor canceling FET parasitic inductance

M. Hieda, K. Nakahara, K. Miyaguchi, H. Kurusu, Y. Iyama, T. Takagi and S. Urasaki. "High-isolation series-shunt FET SPDT switch with a capacitor canceling FET parasitic inductance." 2001 Transactions on Microwave Theory and Techniques 49.12 (Dec. 2001 [T-MTT] (Special Issue on 2001 International Microwave Symposium)): 2453-2458.

A novel series-shunt FET narrow-band high-isolation single-pole double-throw switch, which employs series capacitors to cancel the parasitic inductances has been developed. The proposed switch can have significantly high isolation characteristics at higher frequency. The fabricated two switches have demonstrated high isolation characteristics of 28.9 dB in the 28- and 18-GHz band, respectively.

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